**Product data sheet** 

## 1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

### 2. Features and benefits

- Soft recovery characteristic
- Low switching loss
- Fast switching
- High thermal cycling performance
- Low thermal resistance
- · Low forward voltage drop

# 3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		500				V
I <sub>O(AV)</sub>	average output current	SQW; $\delta$ = 0.5; $T_{mb} \le$ 115 °C; both diodes conducting; Fig. 1; Fig. 2	20			Α	
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 115 °C; per diode	20			Α	
I <sub>FSM</sub>	non-repetitive peak	SIN; $t_p = 10 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; per diode	120			20	
	forward current	SIN; $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; per diode	132				Α
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	$I_F = 10 \text{ A}; T_j = 150 \text{ °C}; Fig. 4$ - 0.87 1.0		1.05	V		
Dynamic	characteristics				,		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6; Fig. 7$		-	50	60	ns

**Dual ultrafast power diode** 

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	1 7 9	[5]
3	A2	anode 2		A1 A2 K sym125

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BYV34-500	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking codes
BYV34-500	BYV34-500

**Dual ultrafast power diode** 

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		500	V
$V_{RWM}$	crest working reverse voltage		500	V
$V_R$	reverse voltage	T <sub>mb</sub> ≤ 138 °C; DC	500	V
$I_{O(AV)}$	average output current	SQW; $\delta$ = 0.5; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2	20	А
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta$ = 0.5; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 115 °C; per diode	20	Α
I <sub>FSM</sub>	non-repetitive peak	SIN; $t_p = 10 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; per diode	120	Α
	forward current	SIN; $t_p = 8.3 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$ ; per diode	132	А
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C

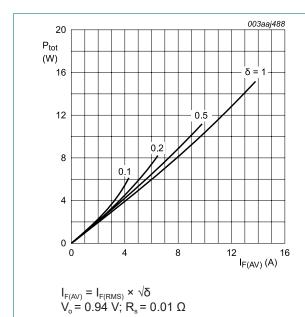
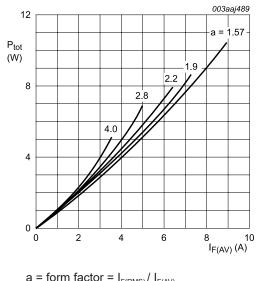


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 0.94 V;  $R_s$  = 0.01  $\Omega$ 

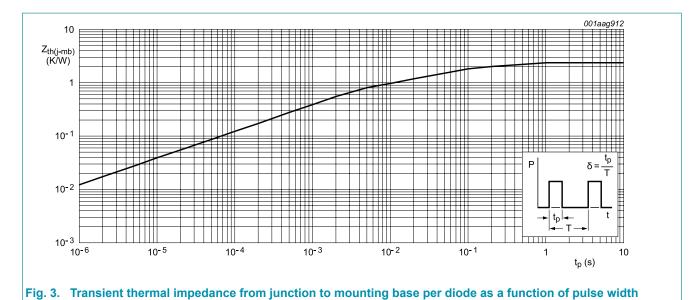
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

**Dual ultrafast power diode** 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	1.6	K/W
	mounting base	with heatsink compound; per diode; Fig. 3	-	-	2.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	60	-	K/W

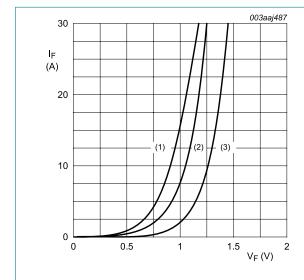


**Dual ultrafast power diode** 

### 10. Characteristics

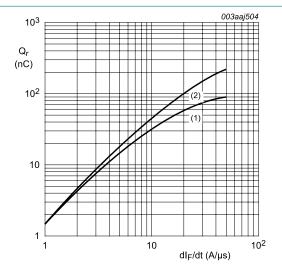
**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Miı	1 Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.1	1.35	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.87	1.05	V
I <sub>R</sub> reverse current		V <sub>R</sub> = 500 V; T <sub>j</sub> = 25 °C	-	10	50	μA
		V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics			'		
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/}\mu\text{s}$ ; Fig. 5; Fig. 6	-	50	50	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 6; Fig. 7	-	50	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 100 \text{ °C; } \underline{\text{Fig. 6; Fig. 8}}$	-	4	5	А
V <sub>FRM</sub>	forward recovery voltage	$I_F = 10 \text{ A}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 9	-	2.5	-	V



(1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values  $V_o$  = 0.94 V;  $R_s$  = 0.01  $\Omega$ 

Fig. 4. Forward current as a function of forward voltage; per diode



(1)  $I_F = 2 \text{ A}$ ;  $T_j = 25 \text{ °C}$ (2)  $I_F = 20 \text{ A}$ ;  $T_j = 25 \text{ °C}$ 

Fig. 5. Recovered charge as a function of rate of change of forward current; per diode; maximum values

#### **Dual ultrafast power diode**

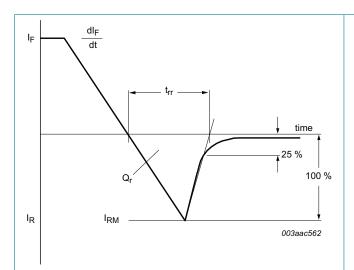
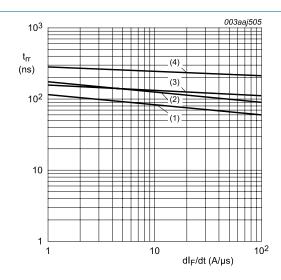


Fig. 6. Reverse recovery definitions; ramp recovery



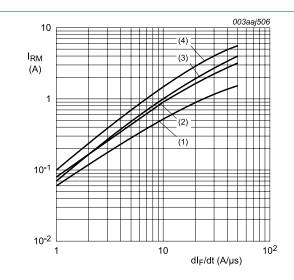
(1) 
$$I_F = 1 A$$
;  $T_j = 25 °C$ 

(2) 
$$I_F = 1 A$$
;  $T_j = 100 °C$ 

(3) 
$$I_F = 20 \text{ A}$$
;  $T_i = 25 \text{ °C}$ 

(4) 
$$I_F = 20 \text{ A}$$
;  $T_j = 100 \text{ °C}$ 

Fig. 7. Reverse recovery time as a function of rate of change of forward current; per diode; maximum values



(1)  $I_F = 1 A$ ;  $T_i = 25 °C$ 

(2) 
$$I_F = 1 A$$
;  $T_j = 100 \,^{\circ}C$ 

(3)  $I_F = 20 \text{ A}$ ;  $T_j = 25 \text{ °C}$ 

(4)  $I_F = 20 \text{ A}$ ;  $T_i = 100 \text{ °C}$ 



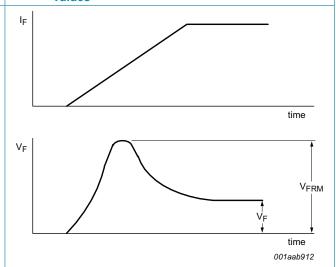


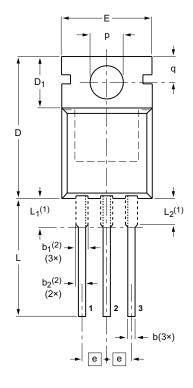
Fig. 9. Forward recovery definitions

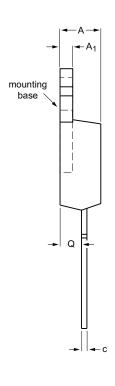
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# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





0 5 10 mm

#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13	

**Product data sheet** 

#### **Dual ultrafast power diode**

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## Dual ultrafast power diode

### 13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	4
10. Characteristics	5
11. Package outline	7
12. Legal information	8
13. Contents	10

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